

# Upgrade of the Inner Tracking System of ALICE

with a focus on pixel sensor development

Monika Kofarago

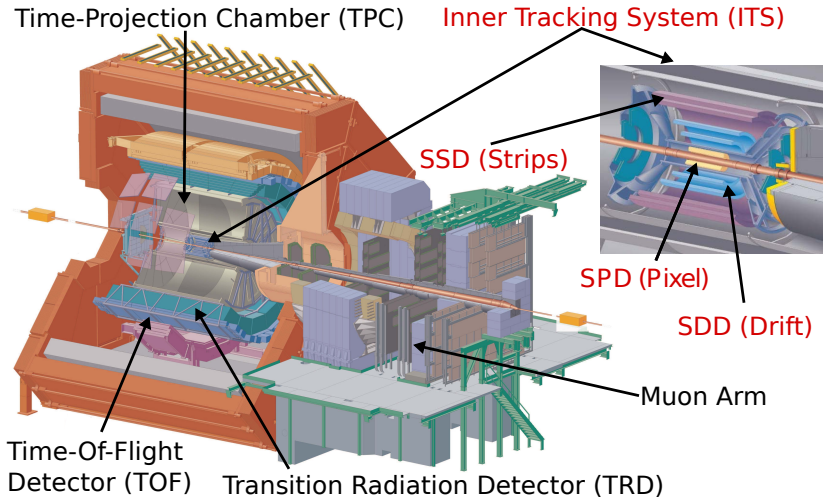
on behalf of the ALICE Collaboration

1st June 2015

24th International Workshop on Vertex Detectors



# A Large Ion Collider Experiment (ALICE)



Talk by Domenico Colella on the current ITS on Monday morning

## Motivations and strategy:

- ALICE was designed to study the **quark-gluon plasma** formed in heavy ion collisions
- High precision measurements of **rare probes at low  $p_T$** 
  - cannot be selected by a hardware trigger
- Record large **minimum bias** samples
  - read out all collisions at the maximum LHC collision rate (50 kHz)
- **Integrated luminosity of  $10 \text{ nb}^{-1}$**  in Pb-Pb (plus pp and p-A data)
  - factor 100 in statistics compared to LHC Run 1 and 2 (2009 - 2018)

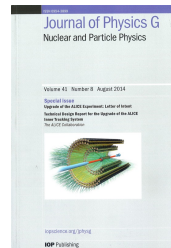
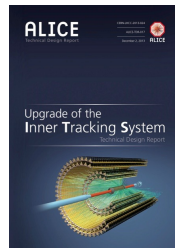
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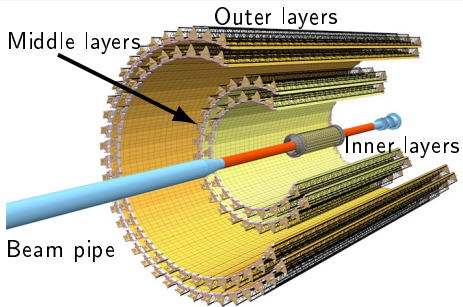
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## Upgrades:

- **New Inner Tracking System (ITS)**
- New Muon Forward Tracker (MFT)
- Smaller beam pipe
- Online and offline system
- Electronics and readout of the Time-Projection Chamber (TPC)
- Readout electronics of several detectors

- Improve impact parameter resolution by a **factor of 3(5)** in  $r\text{-}\varphi(z)$  at  $p_T = 500 \text{ MeV}/c$ 
  - First layer closer to interaction point:  $39 \text{ mm} \rightarrow 23 \text{ mm}$
  - Material budget:  $\sim 1.14\% X_0 \rightarrow 0.3\% X_0$  for the three innermost layers
  - Pixel size:  $50\mu\text{m} \times 425\mu\text{m} \rightarrow O(30\mu\text{m} \times 30\mu\text{m})$
- Improve tracking efficiency and  $p_T$  resolution at low  $p_T$ 
  - 6 layers  $\rightarrow$  7 layers
  - All layers pixel chips (instead of strip, drift and pixel layers)
- Fast readout (now limited to 1 kHz with full ITS)
  - Pb-Pb:  $> 100 \text{ kHz}$
  - pp: **several  $10^5 \text{ Hz}$**
- Fast insertion/removal for yearly maintenance





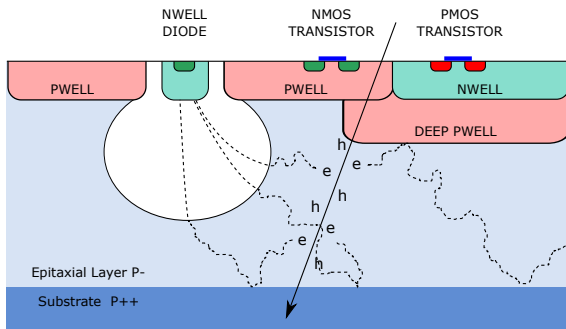
- 7 layers of pixel sensors  
( $r = 23 - 400$  mm)
- $10 \text{ m}^2$  of silicon with 12.5 Gpixels
- $|\eta| < 1.22$  for tracks from 90% of the most luminous region

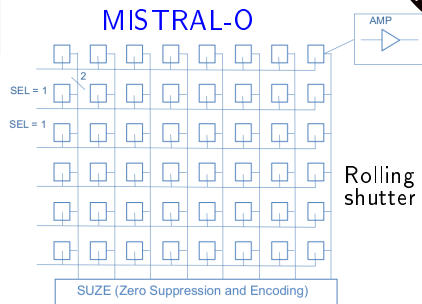
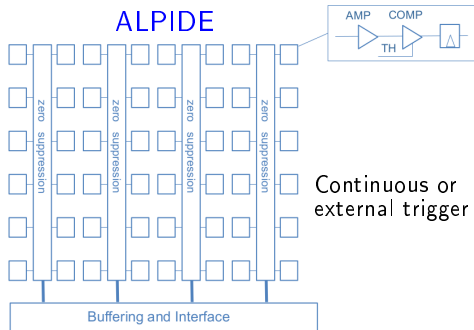
Parameter	Inner barrel	Outer barrel
Silicon thickness		$50 \mu\text{m}$
Spatial resolution	$5 \mu\text{m}$	$10 \mu\text{m}$
Power density	$< 300 \text{ mW/cm}^2$	$< 100 \text{ mW/cm}^2$
Event resolution		$< 30 \mu\text{s}$
Detection efficiency		$> 99\%$
Fake hit rate	$< 10^{-5}$ per event per pixel	
Average track density	$15 - 35 \text{ cm}^{-2}$	$0.1 - 1 \text{ cm}^{-2}$
TID radiation *	2700 krad	100 krad
NIEL radiation *	$1.7 \times 10^{13} \text{ 1 MeV } n_{\text{eq}}/\text{cm}^2$	$10^{12} \text{ 1 MeV } n_{\text{eq}}/\text{cm}^2$

\* Including a safety factor of 10

## Monolithic Active Pixel Sensors using TowerJazz 0.18 $\mu\text{m}$ CMOS imaging process

- High-resistivity ( $> 1\text{k}\Omega\text{ cm}$ ) epitaxial layer on p-type substrate
- Quadruple well process: deep PWELL shields NWELL of PMOS transistors, allowing for full CMOS circuitry within active area
- Moderate reverse substrate biasing is possible, resulting in larger depletion volume around NWELL collection diode





- Readout: Data driven
  - Pixel pitch:  $28\mu\text{m} \times 28\mu\text{m}$
  - Event time resolution:  $\lesssim 2\mu\text{s}$
  - Power consumption:  $39 \text{ mW}/\text{cm}^2$
  - Dead area:  $1.1 \text{ mm} \times 30 \text{ mm}$
- Rolling shutter
  - $36\mu\text{m} \times 65\mu\text{m}$
  - $\sim 20\mu\text{s}$
  - $80 - 90 \text{ mW}/\text{cm}^2$
  - $1.5 \text{ mm} \times 30 \text{ mm}$
- Baseline solution is the ALPIDE
  - Both chips have the same dimensions, identical physical and electrical interfaces



## Existing ALPIDE chip types:

2012 Explorer-0

2013 Explorer-1  
pALPIDEss-0

2014 May pALPIDE-1  
pALPIDEss-1  
Investigator

2015 April pALPIDE-2

2015 August pALPIDE-3

2016 February ALPIDE

### ● **Explorer and Investigator:**

Analog chip to study pixel geometry, starting material and sensitivity to radiation

### ● **pALPIDEss:**

Small scale digital chip to study the priority encoder and the front-end electronics

### ● **pALPIDE-1:**

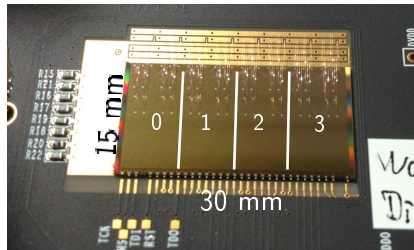
Full scale chip to study system effects

### ● **pALPIDE-2:**

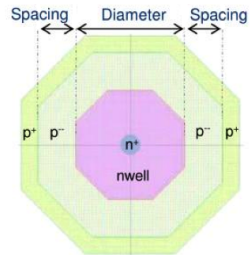
Full scale chip which supports integration into module prototypes:

New pad over logic geometry and support of Outer Barrel local data bus

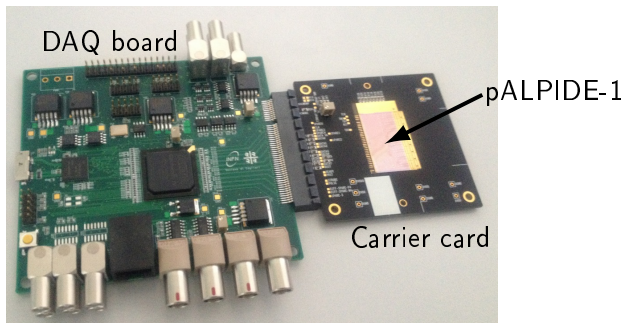
- First prototype with final size (15 mm x 30 mm)
- 512 x 1024 pixels
- Pixels are  $28\mu\text{m} \times 28\mu\text{m}$
- Digital readout with priority encoder
- Four sectors with different pixel layouts

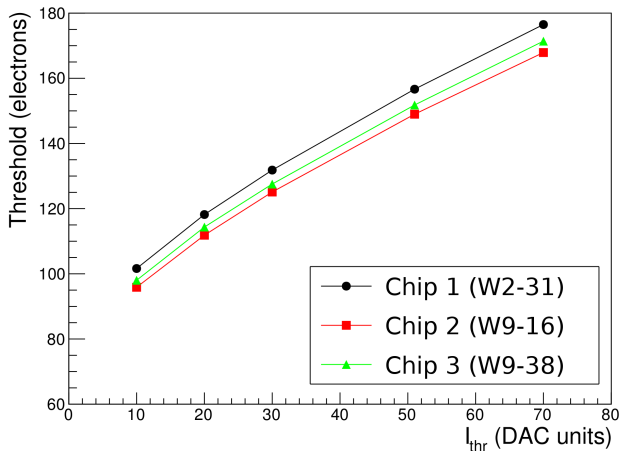


Sector	Nwell diameter	Spacing	Pwell opening	Reset
0	$2\mu\text{m}$	$1\mu\text{m}$	$4\mu\text{m}$	PMOS
1	$2\mu\text{m}$	$2\mu\text{m}$	$6\mu\text{m}$	PMOS
2	$2\mu\text{m}$	$2\mu\text{m}$	$6\mu\text{m}$	Diode
3	$2\mu\text{m}$	$4\mu\text{m}$	$10\mu\text{m}$	PMOS



- Noise and threshold measurements
- Radioactive source measurements
- Noise occupancy measurements
- Several setups:  
CERN, France, Italy, Russia, South Korea, Thailand





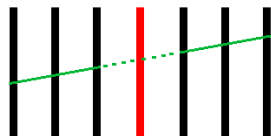
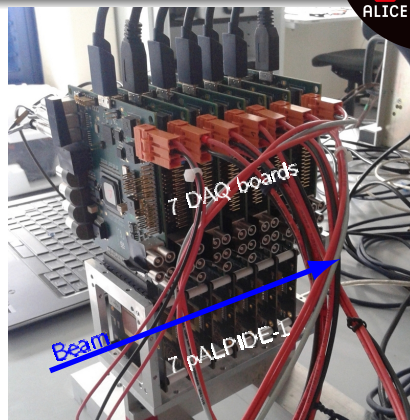
$V_{BB} = -3\text{ V}$   
Sector 2

- Input charge threshold increases as function of  $I_{thr}$
- Threshold spread between pixels: 20 - 50 electrons
- Results are from one sector  $\rightarrow$  fourth of the final chip size

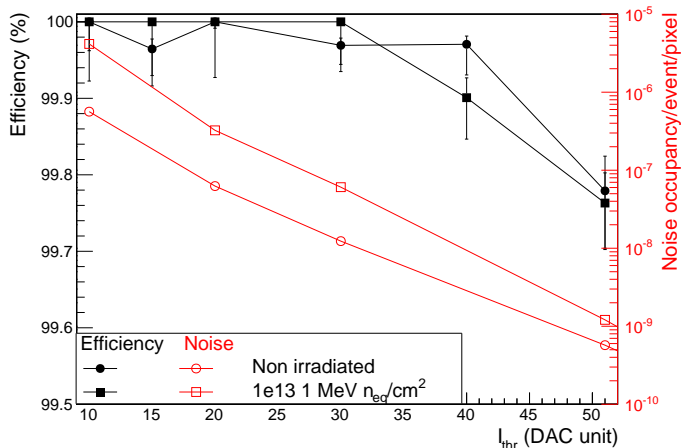
## Test beam

- Tracking is done by a stack of 7 layers of pALPIDE-1
- Readout and analysis is done using the EUDAQ/EUTelescope framework \*
- Several campaigns from 60 MeV to 120 GeV (PS, SPS, DESY, BTF, PAL)
- Measurement of detection efficiency and spatial resolution

\*<https://eutelescope.web.cern.ch>

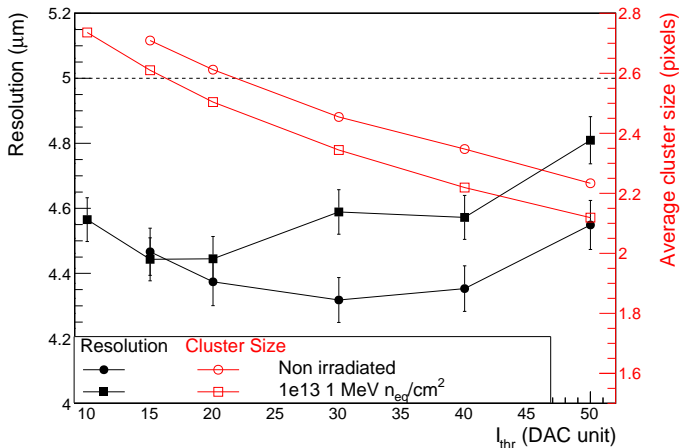


DUT  
Device Under Test



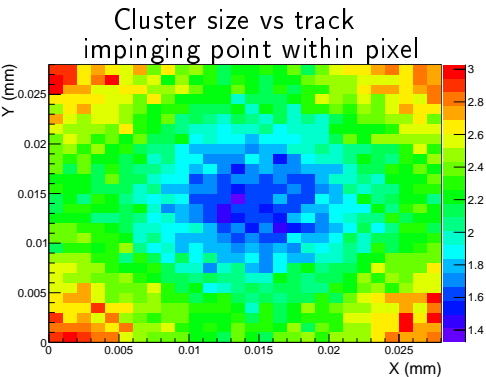
$V_{BB} = -3 V$   
Sector 2  
W9-16, W5-25

- 20 most noisy pixels masked
- Wide operating range with efficiency above 99% and noise occupancy below  $10^{-5}$ /event/pixel
- Slight increase in noise occupancy after irradiation



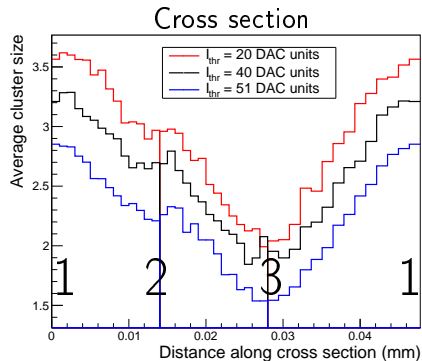
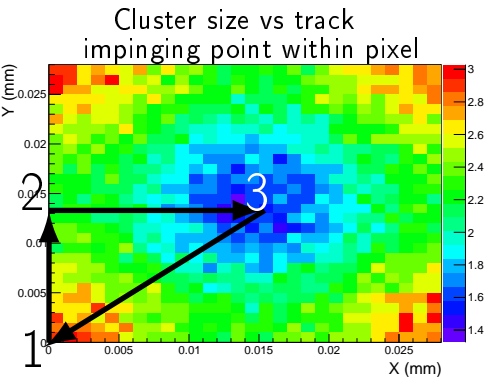
$V_{BB} = -3 \text{ V}$   
Sector 2  
W2-31, W2-12

- Wide operating range with resolution below  $5 \mu\text{m}$
- Resolution becomes slightly worse after irradiation



$V_{BB} = 0 \text{ V}$   
Sector 2  
W2-25



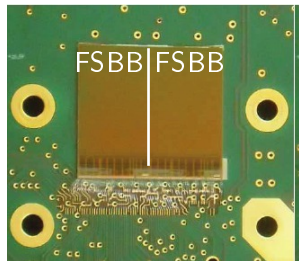


- Clusters size changes with track impinging point as expected from charge sharing

$V_{BB} = 0 \text{ V}$   
Sector 2  
W2-25

## MISTRAL FSBB

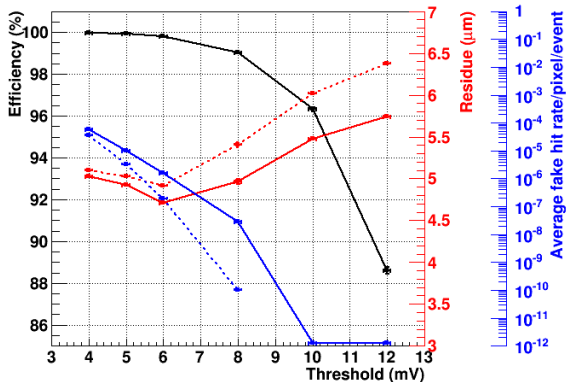
- First Full Scale Building Block (FSBB)
- Sensitive area:  $13.7 \times 9.2\text{mm}^2$  ( $\sim$  third of the final chip size)
- Staggered pixels of  $22 \times 33\mu\text{m}^2$
- In-pixel pre-amplification and clamping with 6 metal layers
- $416 \times 416$  of Columns  $\times$  Row of pixels ended by discriminator (8-cols with analogue output)
- Double-row readout at 160 MHz clock frequency resulting in  $40\mu\text{s}$  integration time



## MISTRAL-O

- Being optimized for the outer layers
  - Target requirements on the spatial resolution:  $\sim 10\mu\text{m}$
  - Target requirements on power consumption:  $< 100\text{mW}/\text{cm}^2$
- Staggered pixels of  $36 \times 65\mu\text{m}^2$
- $20\mu\text{s}$  integration time

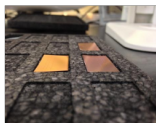
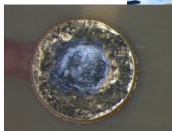
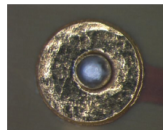
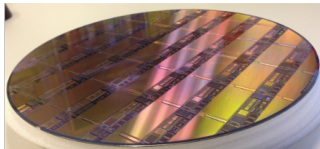
FSBB\_M0a, Diode =  $9 \mu\text{m}^2$ , Transistor = 1.5/0.28



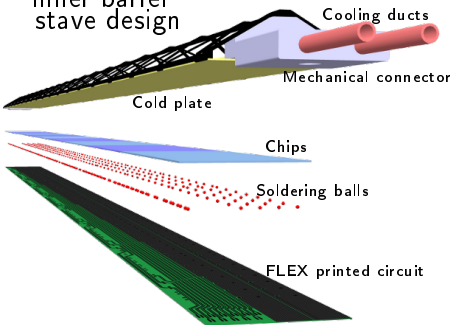
For more information:  
Talk by Michael Deveaux on Friday

- Large operational margin:  $5.0 \text{ mV} \leq \text{Thr} \leq 8.0 \text{ mV}$
- Fake hit rate averaged over 11 sensors
- Fake hit rate drops by  $O(10)$  by masking the 20 noisiest pixel
- Tracking resolution is  $(4.7 \pm 0.1)\mu\text{m}$  (U) and  $(4.9 \pm 0.1)\mu\text{m}$  (V) at  $\text{Thr} = 6 \text{ mV}$

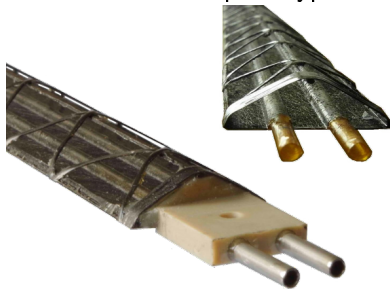
- Inner barrel prototypes and testing
- Outer barrel prototypes and testing
- Cooling
- Assembly machine
- Readout electronics
- Sensor post processing
- Chip transport
- Laser soldering
- Mass testing



## Inner barrel stave design

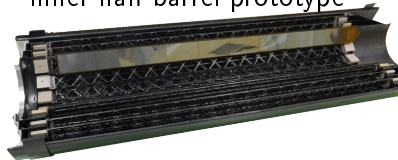


## Inner barrel stave prototypes

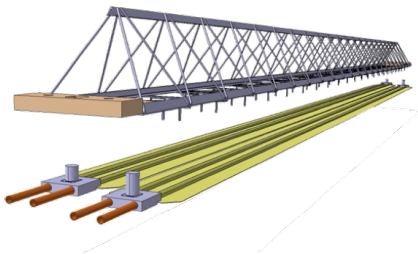


- Material budget:  $\sim 0.3\% X_0$
- Detector operated at room temperature
- Coolant:  $H_2O$
- Chips are laser soldered to FLEX printed circuit

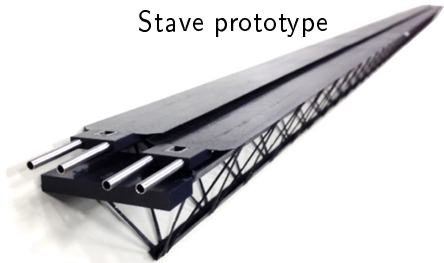
## Inner half barrel prototype



## Stave design

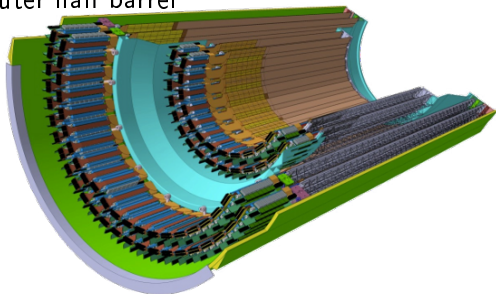


## Stave prototype



- Material budget:  $\sim 1\% X_0$
- Two half staves grouped into one stave

## Outer half barrel

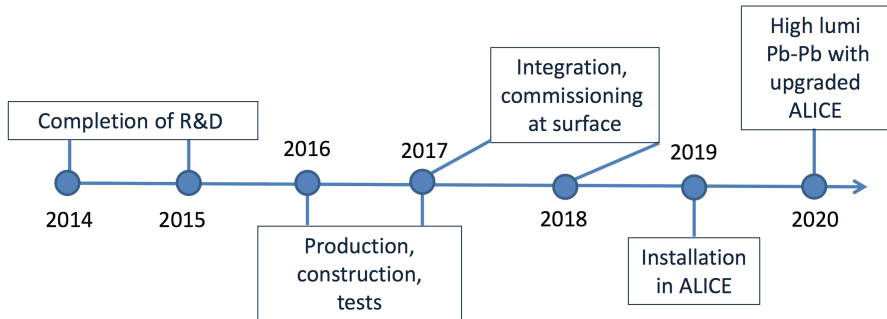


- The Inner Tracking System of ALICE will be replaced during the second long shut down of the LHC (2018/19)
- Impact parameter and tracking resolution and  $p_T$  resolution at low  $p_T$  will improve significantly
- 7 layers of monolithic pixel sensors will be used
- First full scale prototypes show good performance and large margin of operation
- All aspects of the R&D are close to completion and all specifications are possible to meet
- Project is advancing according to schedule

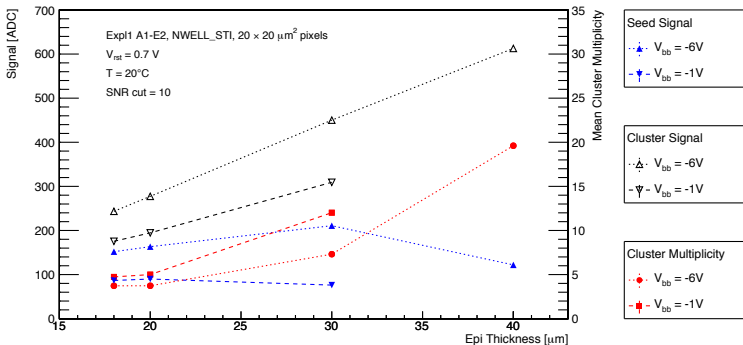
Thank you for your attention!

BACKUP





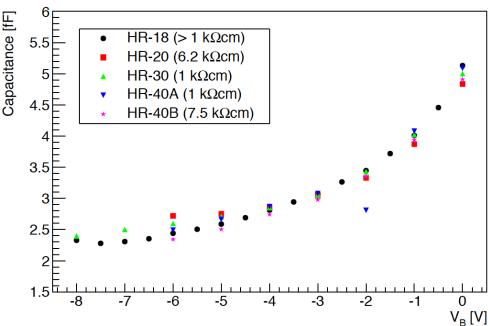
20 × 20 μm<sup>2</sup> pixels:



- Cluster charge increases linearly with epi-layer thickness
- Cluster size increases with epi-layer thickness
- Optimum epi-layer thickness depends on the applied reverse substrate bias

## NWELL diode output signal = $Q/C$

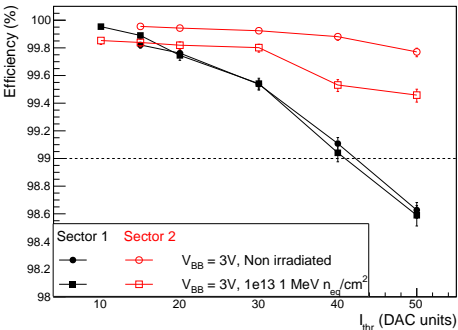
- Minimize spread of charge over many pixels
- Minimize capacitance:
  - Small diode surface
  - Large depletion volume



- Pixel input capacitance decreases with increasing reverse substrate bias
- Minor influence of epi-layer resistivity for current pixel layout

## Effect of reset method

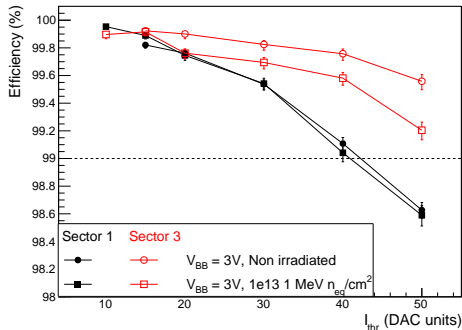
- Sector 1: PMOS reset
- Sector 2: Diode reset



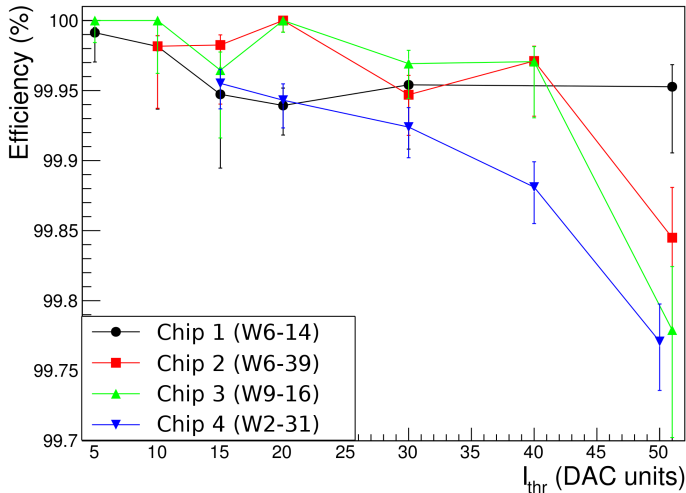
- Diode reset seems to show better performance before and after irradiation
- Diode reset seems to be more effected by irradiation
- Larger spacing seems beneficial

## Effect of spacing

- Sector 1: 2 $\mu$ m
- Sector 3: 4 $\mu$ m



$V_{BB} = -3 V$   
W2-31, W2-12

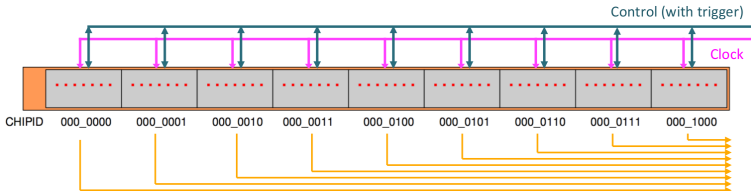


$V_{BB} = -3$  V  
Sector 2

● Chip to chip fluctuations are within statistical fluctuations

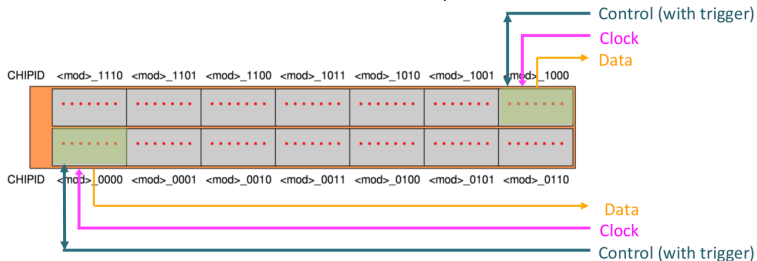
## Inner layers:

- 9 independent sensors (each reads/drives its own data line)

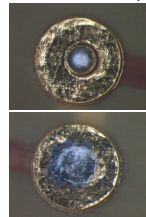
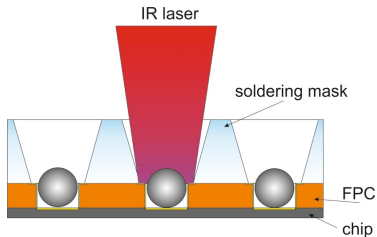


## Mid/outer layers:

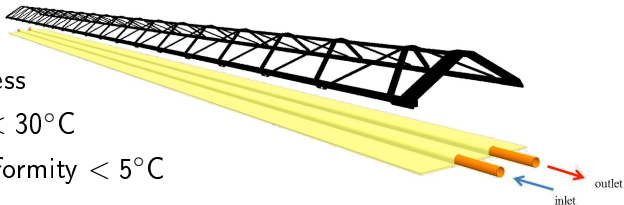
- 2 symmetric group of 1 master and 6 slave chips
- Only the master accesses the data/control lines



- Interconnection of pixel chip with flexible printed circuit
- Both mechanical and electrical connection

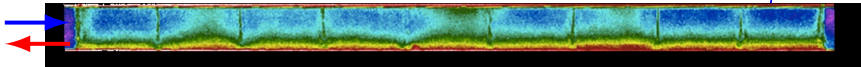


- Coolant: H<sub>2</sub>O, leak-less
- Sensor temperature < 30°C
- Temperature non-uniformity < 5°C



$$T_{in} = 15.8^{\circ}\text{C}$$

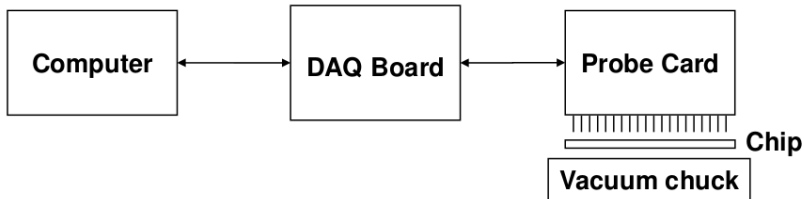
$$\text{Min } T_{pixel} = 16.5^{\circ}\text{C}$$



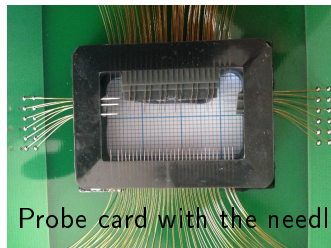
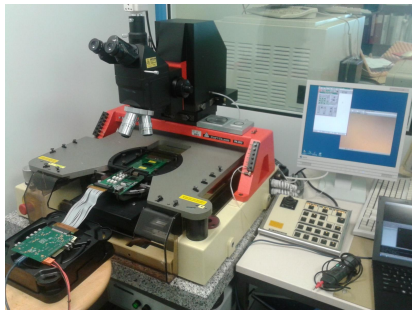
$$T_{out} = 16.6^{\circ}\text{C}$$

$$\text{Max } T_{pixel} = 18.5^{\circ}\text{C}$$

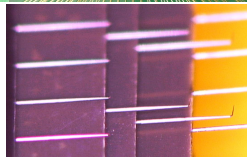




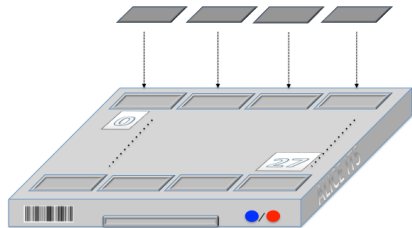
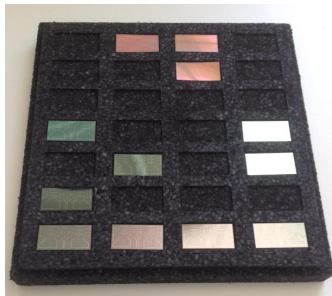
## Probe station prototype

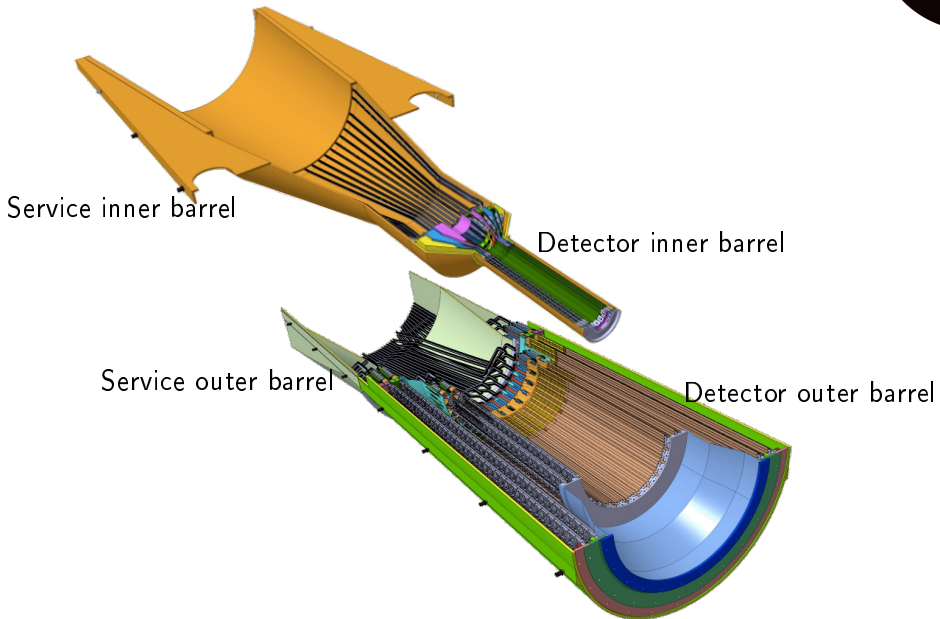


Probe card with the needles

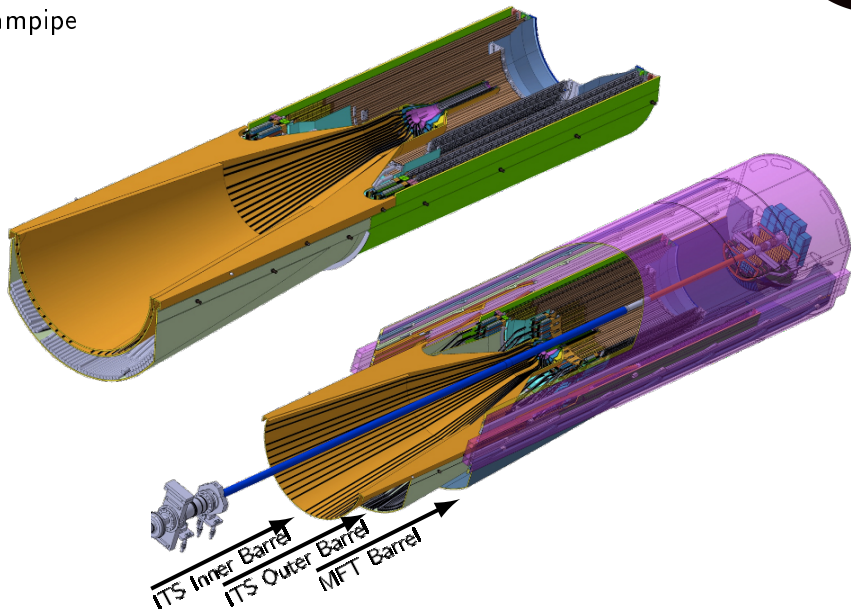


- Assembly will take place in many parts of the world → safe transport method needed
- Transport test from CERN to Pusan (South Korea) and back
- Visual inspection in both places
- Measurement of temperature, acceleration and humidity during the trip
- Chips are back to CERN → No visual damage

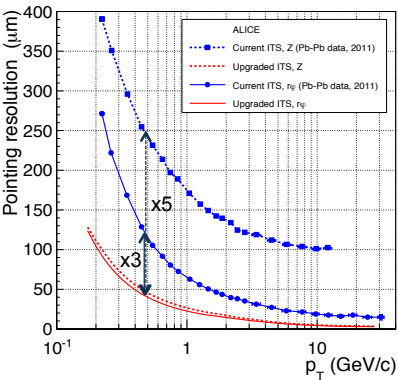




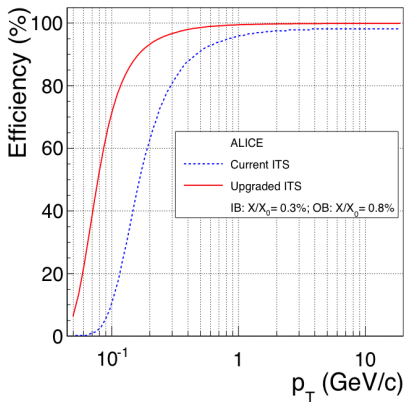
Independent insertion of ITS Inner and Outer half barrel along the beampipe



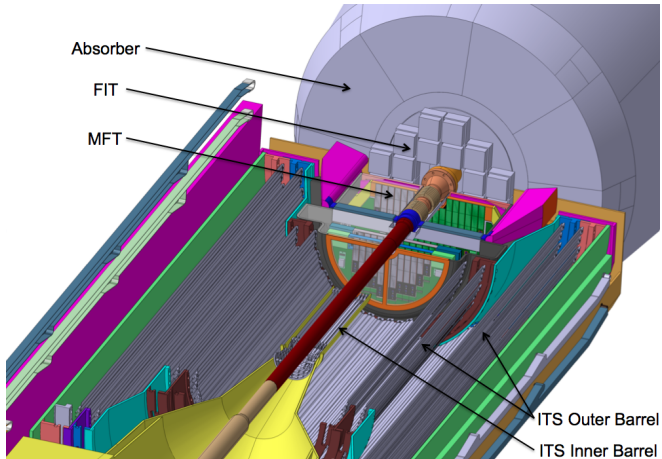
## Impact parameter resolution



## Tracking efficiency (ITS standalone)



- Study QGP physics at forward rapidity in ALICE
- Vertexing for the ALICE Muon Spectrometer (MS) at forward rapidity



- 5 detection disks of silicon pixel sensors  $O(25 \mu\text{m} \times 25 \mu\text{m})$
- 0.6% of  $X_0$  per disk
- TID  $< 400$  krad, NEIL  $< 6 \times 10^{12}$  1 MeV  $n_{\text{eq}}/\text{cm}^2$  (safety factor of 10)



Same chip will be used as for the ITS

- Disk 0 at  $z = -460$  mm,  $R_{\text{in}} = 25$  mm (limited by the beam-pipe radius)
- Disk 4 at  $z = -768$  mm (limited by FIT and the frontal absorber)

